## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

## Electronic Version v18

Stylesheet Version v18.0

Title of Invention

MAGNETIC RANDOM ACCESS MEMORY AND METHOD OF FABRICATING THEREOF

Application Number: 10/604533

7-29.03

Confirmation Number: First Named Applicant:

William Wille

Attorney Docket Number:

FIS920020132US1

Art Unit:

2813

Examiner:

Search string:

( 5695810 or 5804458 or 5920500 or 5936293 or 6147900 or 6165803 or 6351408

or 6365419 or 6381170 or 6396735 or 6048739 ).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

	init	Cite.No.	Patent No.	Date	Patentee Kind		Class	Subclass
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		/, 10	6396735	2002-05-28	Michijima, et al.			
A		11	6048739	2000-04-11	Hurst, et al.			. )

Signature

Examiner Name	Date		
Ex State	12/18/04		

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INFORMATION DISOLOSURE CITATION (Use several ships) if accessary)					Applicants 107604533			3		
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Form PTO-A820 (also form PTO-1449)

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Patent and Trademark Office \* U.S. DEPARTMENT OF COMMERCE

		Docket Number (Options!)	A - W - of - D) A			
<b>l</b>		FIS920020132US1	Application Number			
INFOR	ATION DISCLOSURE CITATION	Applicas(s)				
	(Use several sleets if necessary)	NUETZEL ET AL.	10/604 533			
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